

# NTB6410AN, NTP6410AN, NVB6410AN

## N-Channel Power MOSFET 100 V, 76 A, 13 mΩ

### Features

- Low  $R_{DS(on)}$
- High Current Capability
- 100% Avalanche Tested
- NVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ Unless otherwise specified)

| Parameter                                                                                                                                       | Symbol         | Value                     | Unit             |
|-------------------------------------------------------------------------------------------------------------------------------------------------|----------------|---------------------------|------------------|
| Drain-to-Source Voltage                                                                                                                         | $V_{DS}$       | 100                       | V                |
| Gate-to-Source Voltage – Continuous                                                                                                             | $V_{GS}$       | $\pm 20$                  | V                |
| Continuous Drain Current $R_{\theta JC}$                                                                                                        | $I_D$          | $T_C = 25^\circ\text{C}$  | A                |
|                                                                                                                                                 |                | $T_C = 100^\circ\text{C}$ |                  |
| Power Dissipation $R_{\theta JC}$                                                                                                               | $P_D$          | $T_C = 25^\circ\text{C}$  | W                |
|                                                                                                                                                 |                |                           |                  |
| Pulsed Drain Current                                                                                                                            | $I_{DM}$       | 305                       | A                |
| Operating Junction and Storage Temperature Range                                                                                                | $T_J, T_{stg}$ | $-55$ to $+175$           | $^\circ\text{C}$ |
| Source Current (Body Diode)                                                                                                                     | $I_S$          | 76                        | A                |
| Single Pulse Drain-to-Source Avalanche Energy ( $V_{DD} = 50$ Vdc, $V_{GS} = 10$ Vdc, $I_{L(pk)} = 57.7$ A, $L = 0.3$ mH, $R_G = 25$ $\Omega$ ) | $E_{AS}$       | 500                       | mJ               |
| Lead Temperature for Soldering Purposes, 1/8" from Case for 10 Seconds                                                                          | $T_L$          | 260                       | $^\circ\text{C}$ |

### THERMAL RESISTANCE RATINGS

| Parameter                             | Symbol          | Max | Unit               |
|---------------------------------------|-----------------|-----|--------------------|
| Junction-to-Case (Drain) Steady State | $R_{\theta JC}$ | 0.8 | $^\circ\text{C/W}$ |
| Junction-to-Ambient (Note 1)          | $R_{\theta JA}$ | 32  |                    |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 sq in pad size, (Cu Area 1.127 sq in [2 oz] including traces).

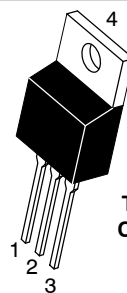
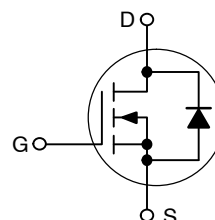


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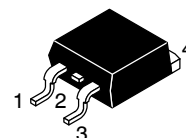
<http://onsemi.com>

| $V_{(BR)DSS}$ | $R_{DS(ON)} \text{ MAX}$ | $I_D \text{ MAX}$<br>(Note 1) |
|---------------|--------------------------|-------------------------------|
| 100 V         | 13 mΩ @ 10 V             | 76 A                          |

### N-Channel

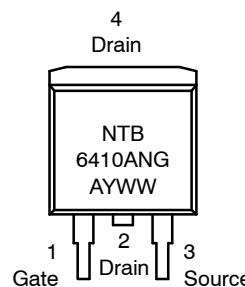
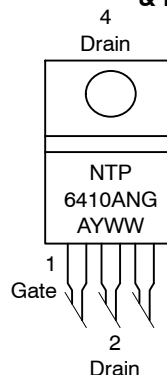


TO-220AB  
CASE 221A  
STYLE 5



D2PAK  
CASE 418B  
STYLE 2

### MARKING DIAGRAM & PIN ASSIGNMENT



6410AN = Specific Device Code  
G = Pb-Free Device  
A = Assembly Location  
Y = Year  
WW = Work Week

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

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## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C Unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------------|--------|----------------|-----|-----|-----|------|
|-----------------|--------|----------------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                                           |                                      |                                                   |                        |    |      |       |
|-----------------------------------------------------------|--------------------------------------|---------------------------------------------------|------------------------|----|------|-------|
| Drain-to-Source Breakdown Voltage                         | V <sub>(BR)DSS</sub>                 | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA    | 100                    |    |      | V     |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | V <sub>(BR)DSS</sub> /T <sub>J</sub> |                                                   |                        | 94 |      | mV/°C |
| Zero Gate Voltage Drain Current                           | I <sub>DSS</sub>                     | V <sub>GS</sub> = 0 V,<br>V <sub>DS</sub> = 100 V | T <sub>J</sub> = 25°C  |    | 1.0  | μA    |
|                                                           |                                      |                                                   | T <sub>J</sub> = 150°C |    | 100  |       |
| Gate-to-Source Leakage Current                            | I <sub>GSS</sub>                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V    |                        |    | ±100 | nA    |

### ON CHARACTERISTICS (Note 2)

|                                            |                                     |                                                             |     |     |     |       |
|--------------------------------------------|-------------------------------------|-------------------------------------------------------------|-----|-----|-----|-------|
| Gate Threshold Voltage                     | V <sub>GS(th)</sub>                 | V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA | 2.0 |     | 4.0 | V     |
| Negative Threshold Temperature Coefficient | V <sub>GS(th)</sub> /T <sub>J</sub> |                                                             |     | 9.0 |     | mV/°C |
| Drain-to-Source On-Resistance              | R <sub>DS(on)</sub>                 | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 76 A               |     | 11  | 13  | mΩ    |
|                                            |                                     | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A               |     | 10  | 12  |       |
| Forward Transconductance                   | g <sub>FS</sub>                     | V <sub>DS</sub> = 5 V, I <sub>D</sub> = 20 A                |     | 40  |     | S     |

### CHARGES, CAPACITANCES & GATE RESISTANCE

|                              |                     |                                                                          |  |      |  |    |
|------------------------------|---------------------|--------------------------------------------------------------------------|--|------|--|----|
| Input Capacitance            | C <sub>iss</sub>    | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,<br>f = 1 MHz              |  | 4500 |  | pF |
| Output Capacitance           | C <sub>oss</sub>    |                                                                          |  | 650  |  |    |
| Reverse Transfer Capacitance | C <sub>rss</sub>    |                                                                          |  | 250  |  |    |
| Total Gate Charge            | Q <sub>G(TOT)</sub> | V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 80 V,<br>I <sub>D</sub> = 76 A |  | 120  |  | nC |
| Threshold Gate Charge        | Q <sub>G(TH)</sub>  |                                                                          |  | 5.2  |  |    |
| Gate-to-Source Charge        | Q <sub>GS</sub>     |                                                                          |  | 20   |  |    |
| Gate-to-Drain Charge         | Q <sub>GD</sub>     |                                                                          |  | 57   |  |    |
| Plateau Voltage              | V <sub>GP</sub>     |                                                                          |  | 5.1  |  | V  |
| Gate Resistance              | R <sub>G</sub>      |                                                                          |  | 2.4  |  | Ω  |

### SWITCHING CHARACTERISTICS, V<sub>GS</sub> = 10 V (Note 3)

|                     |                     |                                                                                                  |  |     |  |    |
|---------------------|---------------------|--------------------------------------------------------------------------------------------------|--|-----|--|----|
| Turn-On Delay Time  | t <sub>d(on)</sub>  | V <sub>GS</sub> = 10 V, V <sub>DD</sub> = 80 V,<br>I <sub>D</sub> = 76 A, R <sub>G</sub> = 6.2 Ω |  | 17  |  | ns |
| Rise Time           | t <sub>r</sub>      |                                                                                                  |  | 170 |  |    |
| Turn-Off Delay Time | t <sub>d(off)</sub> |                                                                                                  |  | 120 |  |    |
| Fall Time           | t <sub>f</sub>      |                                                                                                  |  | 190 |  |    |

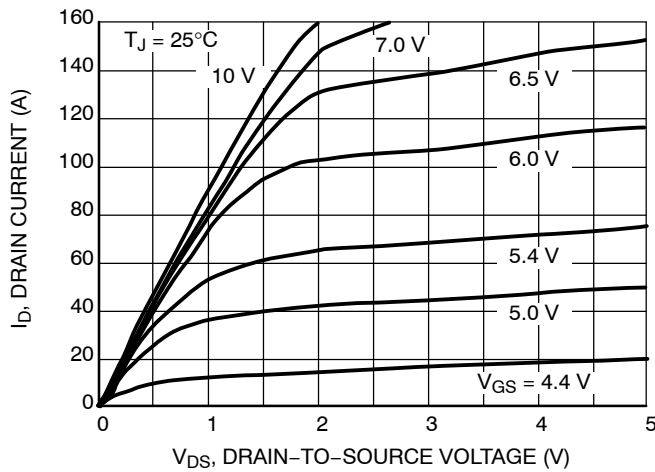
### DRAIN-SOURCE DIODE CHARACTERISTICS

|                         |                 |                                                                                  |                        |     |     |     |    |
|-------------------------|-----------------|----------------------------------------------------------------------------------|------------------------|-----|-----|-----|----|
| Forward Diode Voltage   | V <sub>SD</sub> | I <sub>S</sub> = 76 A                                                            | T <sub>J</sub> = 25°C  |     | 1.0 | 1.3 | V  |
|                         |                 |                                                                                  | T <sub>J</sub> = 125°C |     | 0.9 |     |    |
| Reverse Recovery Time   | t <sub>rr</sub> | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 76 A,<br>di <sub>SD</sub> /dt = 100 A/μs |                        | 93  |     |     | ns |
| Charge Time             | t <sub>a</sub>  |                                                                                  |                        | 69  |     |     |    |
| Discharge Time          | t <sub>b</sub>  |                                                                                  |                        | 24  |     |     |    |
| Reverse Recovery Charge | Q <sub>RR</sub> |                                                                                  |                        | 300 |     |     | nC |

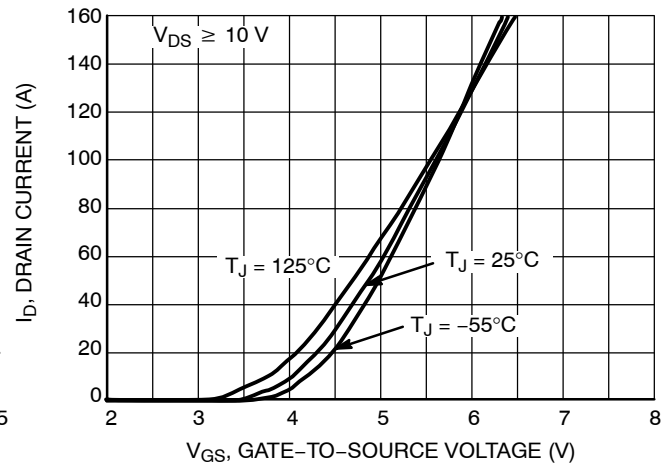
2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

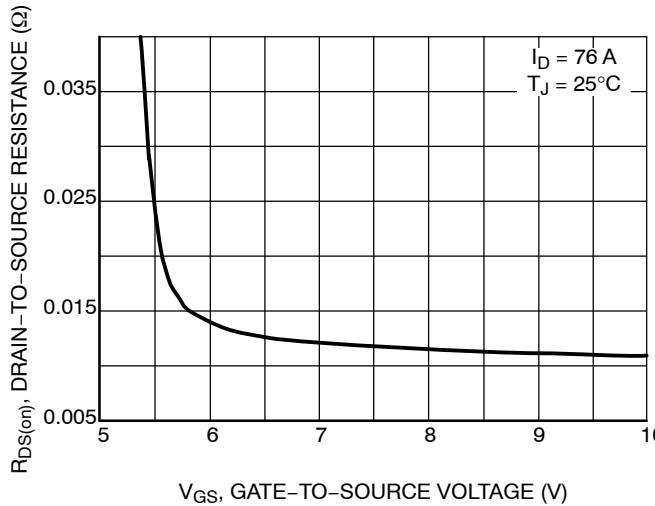
# NTB6410AN, NTP6410AN, NVB6410AN



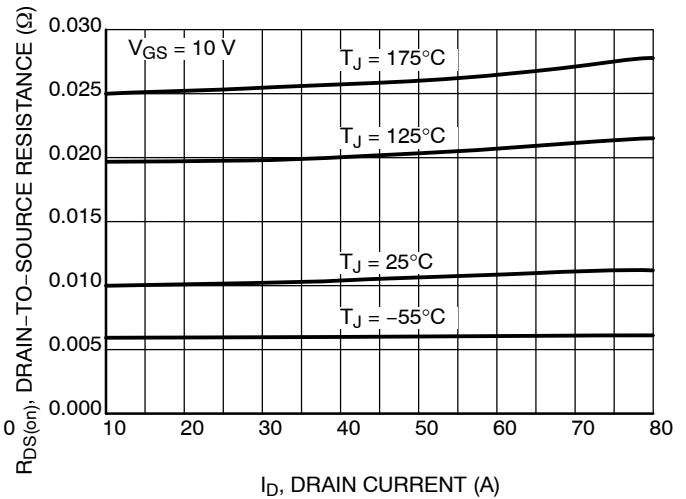
**Figure 1. On-Region Characteristics**



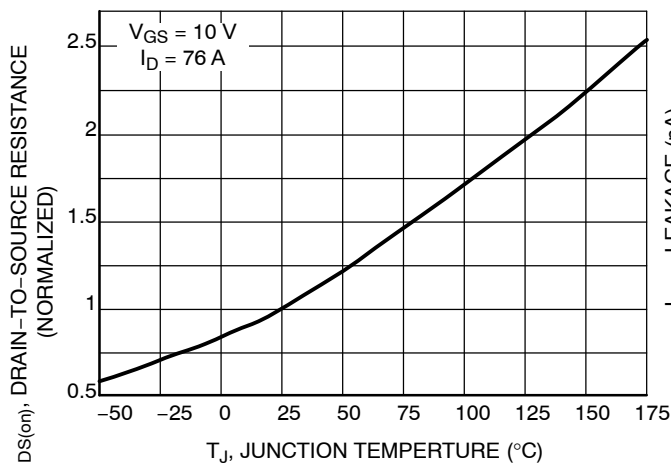
**Figure 2. Transfer Characteristics**



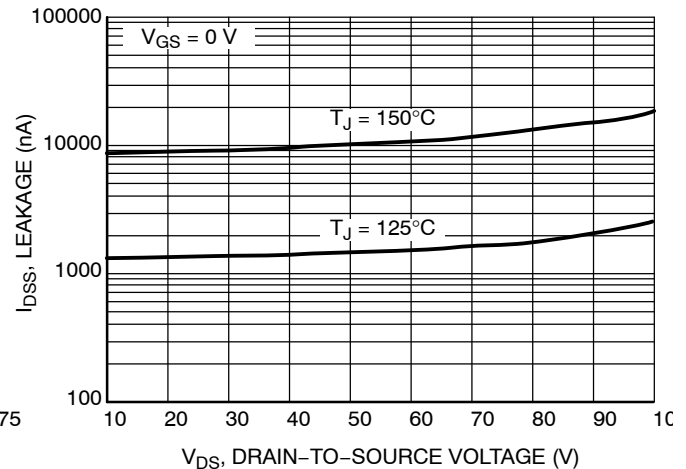
**Figure 3. On-Region versus Gate Voltage**



**Figure 4. On-Region versus Drain Current and Gate Voltage**



**Figure 5. On-Resistance Variation with Temperature**



**Figure 6. Drain-to-Source Leakage Current versus Voltage**

# NTB6410AN, NTP6410AN, NVB6410AN

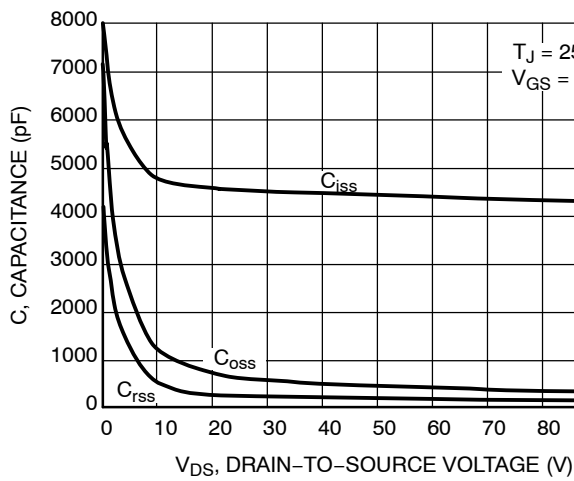


Figure 7. Capacitance Variation

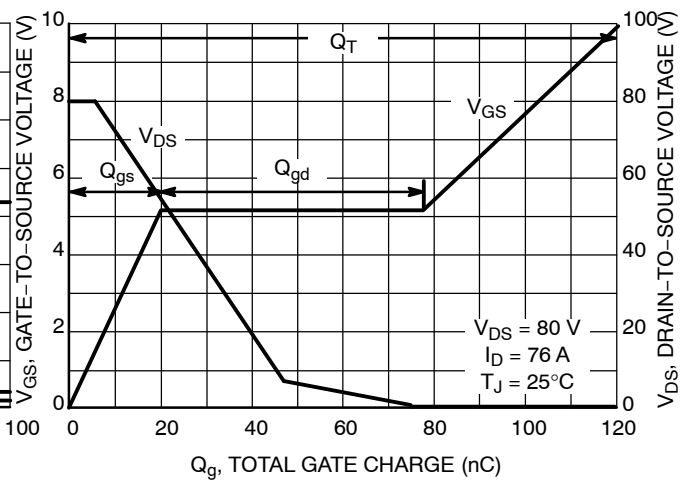


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

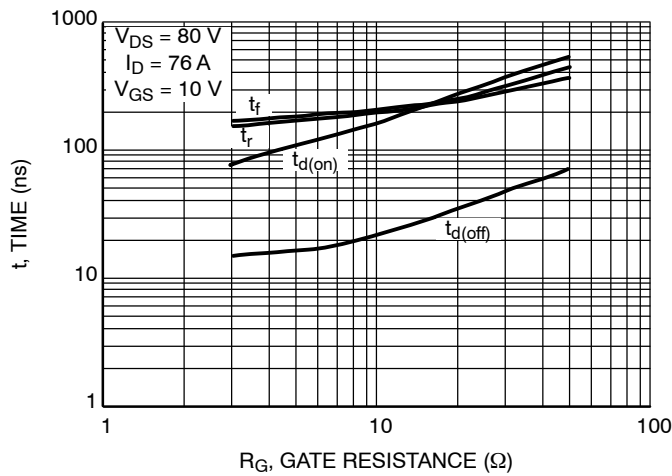


Figure 9. Resistive Switching Time Variation versus Gate Resistance

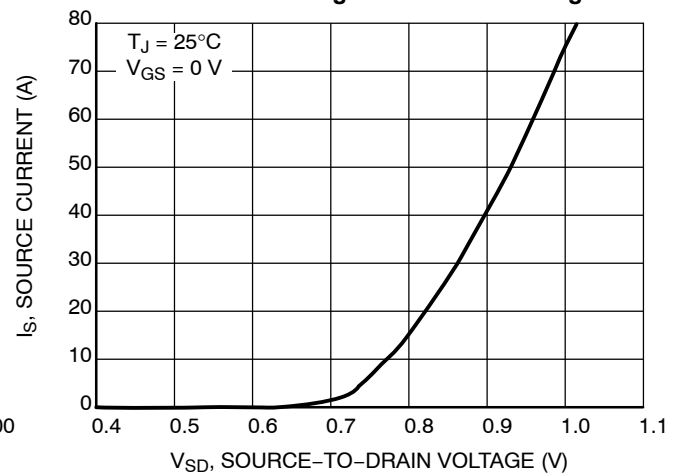


Figure 10. Diode Forward Voltage versus Current

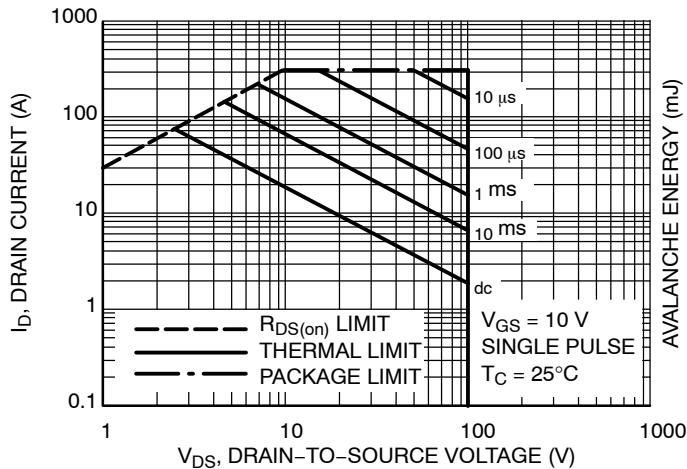


Figure 11. Maximum Rated Forward Biased Safe Operating Area

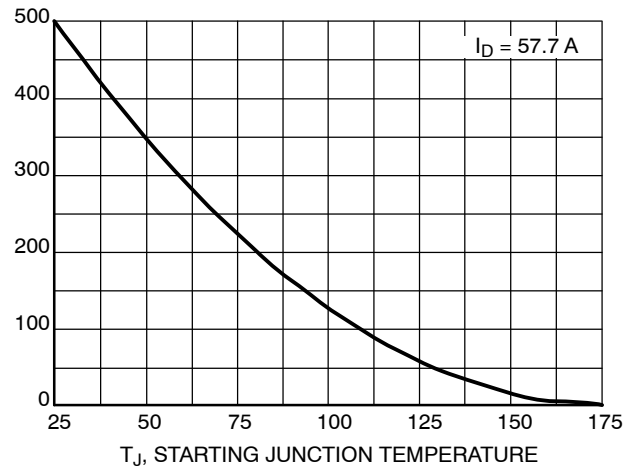


Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature

## NTB6410AN, NTP6410AN, NVB6410AN

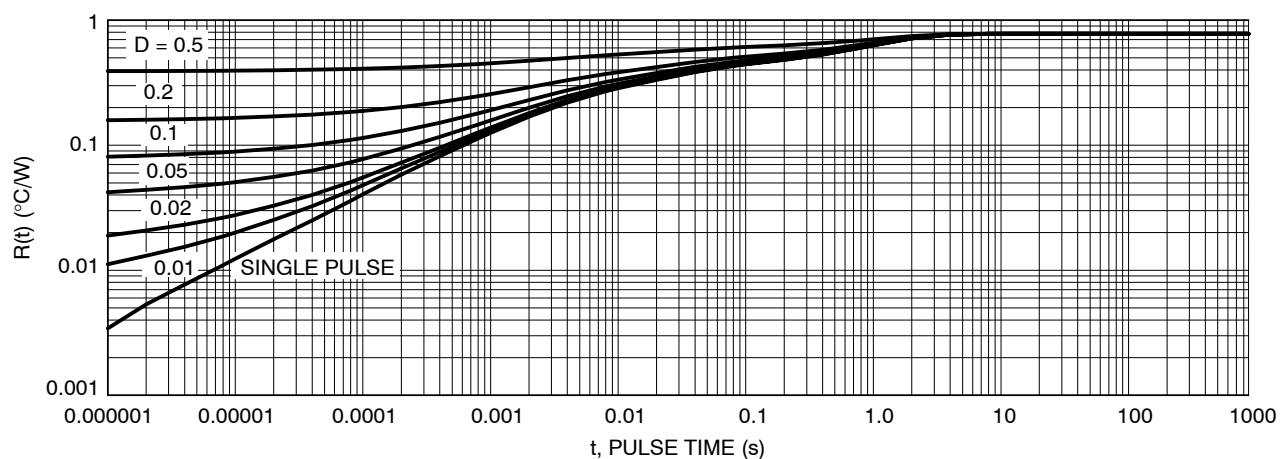


Figure 13. Thermal Response

### ORDERING INFORMATION

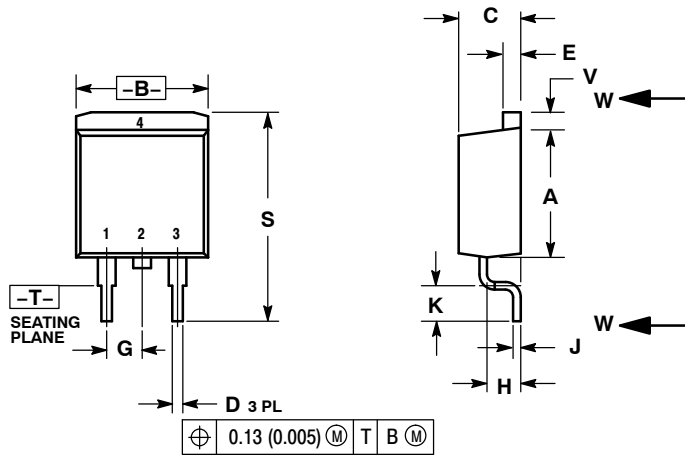
| Device       | Package                         | Shipping <sup>†</sup> |
|--------------|---------------------------------|-----------------------|
| NTB6410ANG   | D <sup>2</sup> PAK<br>(Pb-Free) | 50 Units / Rail       |
| NTB6410ANT4G | D <sup>2</sup> PAK<br>(Pb-Free) | 800 / Tape & Reel     |
| NTP6410ANG   | TO-220<br>(Pb-Free)             | 50 Units / Rail       |
| NVB6410ANT4G | D <sup>2</sup> PAK<br>(Pb-Free) | 800 / Tape & Reel     |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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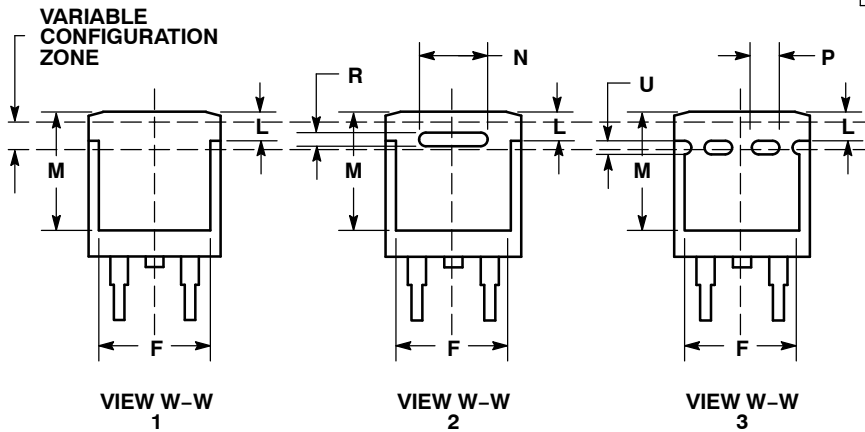
## PACKAGE DIMENSIONS

### D<sup>2</sup>PAK 3 CASE 418B-04 ISSUE K



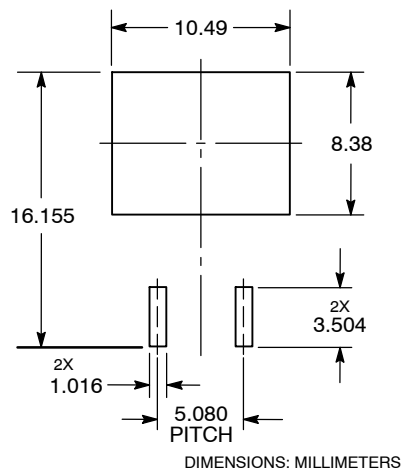
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

| DIM | INCHES    |       | MILLIMETERS |       |
|-----|-----------|-------|-------------|-------|
|     | MIN       | MAX   | MIN         | MAX   |
| A   | 0.340     | 0.380 | 8.64        | 9.65  |
| B   | 0.380     | 0.405 | 9.65        | 10.29 |
| C   | 0.160     | 0.190 | 4.06        | 4.83  |
| D   | 0.020     | 0.035 | 0.51        | 0.89  |
| E   | 0.045     | 0.055 | 1.14        | 1.40  |
| F   | 0.310     | 0.350 | 7.87        | 8.89  |
| G   | 0.100 BSC |       | 2.54 BSC    |       |
| H   | 0.080     | 0.110 | 2.03        | 2.79  |
| J   | 0.018     | 0.025 | 0.46        | 0.64  |
| K   | 0.090     | 0.110 | 2.29        | 2.79  |
| L   | 0.052     | 0.072 | 1.32        | 1.83  |
| M   | 0.280     | 0.320 | 7.11        | 8.13  |
| N   | 0.197 REF |       | 5.00 REF    |       |
| P   | 0.079 REF |       | 2.00 REF    |       |
| R   | 0.039 REF |       | 0.99 REF    |       |
| S   | 0.575     | 0.625 | 14.60       | 15.88 |
| V   | 0.045     | 0.055 | 1.14        | 1.40  |



- STYLE 2:
- PIN 1. GATE
  2. DRAIN
  3. SOURCE
  4. DRAIN

### SOLDERING FOOTPRINT\*

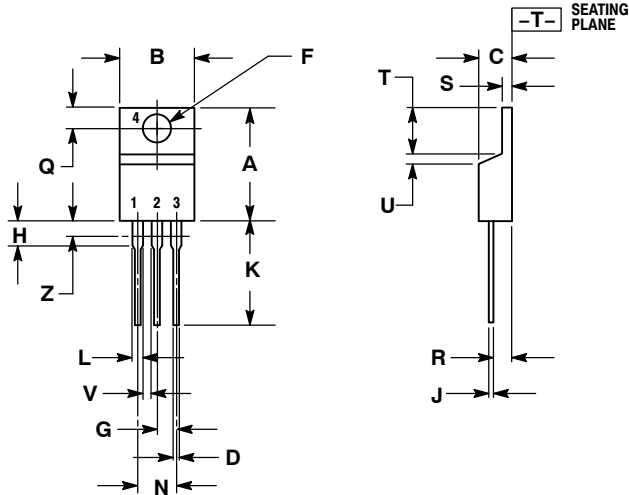


\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# NTB6410AN, NTP6410AN, NVB6410AN

## PACKAGE DIMENSIONS

TO-220  
CASE 221A-09  
ISSUE AG



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| DIM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN    | MAX   | MIN         | MAX   |
| A   | 0.570  | 0.620 | 14.48       | 15.75 |
| B   | 0.380  | 0.405 | 9.66        | 10.28 |
| C   | 0.160  | 0.190 | 4.07        | 4.82  |
| D   | 0.025  | 0.036 | 0.64        | 0.91  |
| F   | 0.142  | 0.161 | 3.61        | 4.09  |
| G   | 0.095  | 0.105 | 2.42        | 2.66  |
| H   | 0.110  | 0.161 | 2.80        | 4.10  |
| J   | 0.014  | 0.025 | 0.36        | 0.64  |
| K   | 0.500  | 0.562 | 12.70       | 14.27 |
| L   | 0.045  | 0.060 | 1.15        | 1.52  |
| N   | 0.190  | 0.210 | 4.83        | 5.33  |
| Q   | 0.100  | 0.120 | 2.54        | 3.04  |
| R   | 0.080  | 0.110 | 2.04        | 2.79  |
| S   | 0.045  | 0.055 | 1.15        | 1.39  |
| T   | 0.235  | 0.255 | 5.97        | 6.47  |
| U   | 0.000  | 0.050 | 0.00        | 1.27  |
| V   | 0.045  | ---   | 1.15        | ---   |
| Z   | ---    | 0.080 | ---         | 2.04  |

### STYLE 4:

- PIN 1. MAIN TERMINAL 1
- MAIN TERMINAL 2
- GATE
- MAIN TERMINAL 2

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